

PNP Silicon Transistors

SIEMENS AKTIENGESELLSCHAFT

BD 136

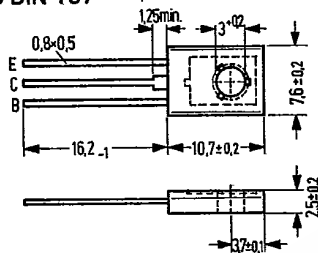
BD 138

BD 140

For AF driver and output stages of medium performance

BD 136, BD 138, and BD 140 are epitaxial PNP silicon planar transistors in TO 126 plastic package (12 A 3 DIN 41869, sheet 4). The collector is electrically connected to the metallic mounting area. Together with BD 135, BD 137, and BD 139 as complementary pairs the transistors BD 136, BD 138, and BD 140 are designed for use in driver stages of high performance AF amplifiers.

Type	Ordering code	Type	Ordering code
BD 136	Q62702-D107	Mica washer	Q62902-B62
BD 136-6	Q62702-D107-V1	Spring washer	Q62902-B63
BD 136-10	Q62702-D107-V2	A 3 DIN 137	
BD 136-16	Q62702-D107-V3		
BD 136 paired	Q62702-D107-P		
BD 138	Q62702-D109		
BD 138-6	Q62702-D109-V1		
BD 138-10	Q62702-D109-V2		
BD 138 paired	Q62702-D109-P		
BD 140	Q62702-D111		
BD 140-6	Q62702-D111-V1		
BD 140-10	Q62702-D111-V2		
BD 140 paired	Q62702-D111-P		
BD 136/135 compl. paired	Q62702-D139-S1		
BD 138/137 compl. paired	Q62702-D140-S1		
BD 140/139 compl. paired	Q62702-D141-S1		



Approx. weight 0.5 g Dimensions in mm

Transistor fixing with M 3 screw. Starting torque max 0.8 Nm. Below the screw head, a washer or spring washer should be used.
1) If a 60 μ mica washer (ungreased) is used, the thermal resistance increases by 8 K/W and in case of a greased one by 4 K/W.

Maximum ratings

Collector-emitter voltage

 $(R_{BE} \leq 1 \text{ k}\Omega)$ $-V_{CER}$

—

—

100

V

Collector-base voltage

 $-V_{CBO}$

45

60

—

V

Collector-emitter voltage

 $-V_{CEO}$

45

60

80

V

Emitter-base voltage

 $-V_{EBO}$

5

5

5

V

Collector peak current

 $-I_{CM}$

2.0

2.0

2.0

A

Collector current

 $-I_C$

1.5

1.5

1.5

A

Base current

 $-I_B$

0.2

0.2

0.2

A

Junction temperature

 T_j

150

150

150

°C

Storage temperature range

 T_{stg}

—55 to +125

°C

Total power dissipation ($T_{case} \leq 25^\circ\text{C}$) P_{tot}

12.5

12.5

12.5

W

Thermal resistance

Junction to ambient air

 R_{thJA} ≤ 110 ≤ 110 ≤ 110

K/W

Junction to case bottom

 R_{thJC} ≤ 10 ≤ 10 ≤ 10

K/W

25C D ■ 8235605 0004338 5 ■ SIEG D T-33-17

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BD 136
BD 138
BD 140

Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

The transistors BD 136, BD 138, and BD 140 are grouped according to the DC current gain h_{FE} and marked by numerals of the German DIN standard.

h_{FE} group	6	10	16	
Type	BD 136 BD 138 BD 140	BD 136 BD 138 BD 140	BD 136 — —	BD 136 BD 138 BD 140
$-I_C$ (mA)	h_{FE} I_C/I_B	h_{FE} I_C/I_B	h_{FE} I_C/I_B	$-V_{BE}$ (V)
5	> 25	> 25	> 25	—
150	63 (40 to 100)	100 (63 to 160)	160 (100 to 250)	—
500	> 25	> 25	> 25	1.2

Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

	BD 136	BD 138	BD 140	
Collector-emitter-saturation voltage ($-I_C = 500\text{ mA}$; $-I_B = 500\text{ mA}$)	$-V_{CEsat}$	< 0.5	> 0.5	< 0.5 V
Collector cutoff current ($-V_{CB} = 30\text{ V}$)	$-I_{CBO}$	< 100	< 100	< 100 nA
Collector cutoff current ($-V_{CB} = 30\text{ V}$; $T_{amb} = 125^{\circ}\text{C}$)	$-I_{CBO}$	≤ 10	≤ 10	$\leq 10\text{ }\mu\text{A}$
Emitter cutoff current ($-V_{EB} = 5\text{ V}$)	$-I_{EBO}$	≤ 10	≤ 10	$\leq 10\text{ }\mu\text{A}$
Collector-emitter breakdown voltage ($-I_{CEO} = 50\text{ mA}$)	$-V_{(BR)CEO}$	> 45	> 60	> 80 V
Condition for matching pairs ($-I_C = 150\text{ mA}$; $-V_{CE} = 2\text{ V}$)	$\frac{h_{FE1}}{h_{FE2}}$	≤ 1.41	≤ 1.41	≤ 1.41
Dynamic characteristics ($T_{amb} = 25^{\circ}\text{C}$)				
Transition frequency ($-I_C = 50\text{ mA}$; $-V_{CE} = 10\text{ V}$; $f = 100\text{ MHz}$)	f_T	> 75	> 75	> 75 MHz

25C D ■ 8235605 0004339 7 ■ SIEG

25C 04339

D

T-33-17

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BD 136

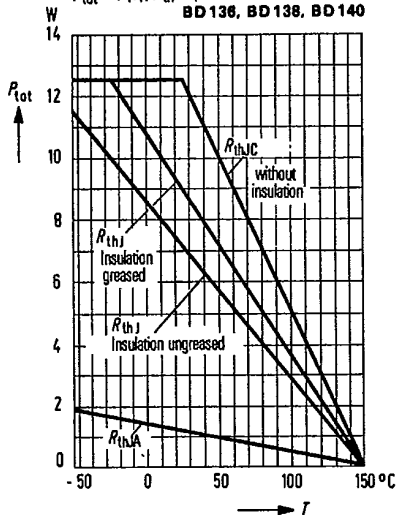
BD 138

BD 140

Total perm. power dissipation
versus temperature

$P_{\text{tot}} = f(T)$; R_{th} = parameter

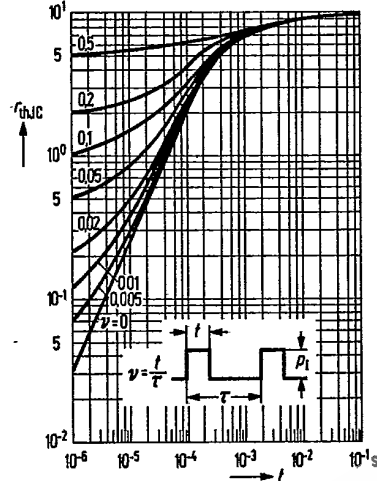
BD 136, BD 138, BD 140



Permissible pulse load

$r_{\text{thJC}} = f(t)$; v = parameter

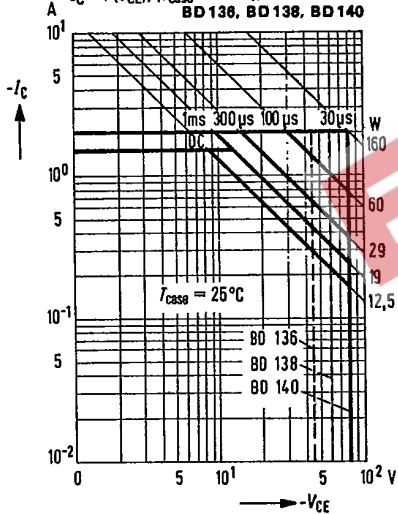
BD 136, BD 138, BD 140



Permissible operating range

$I_C = f(V_{CE})$; ($T_{\text{case}} = 60^\circ\text{C}$); $v = 0$

BD 136, BD 138, BD 140

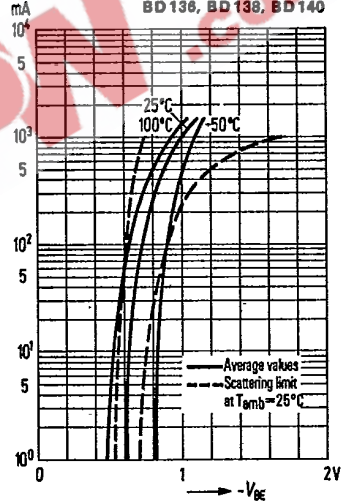


Collector current $I_C = f(V_{CE})$

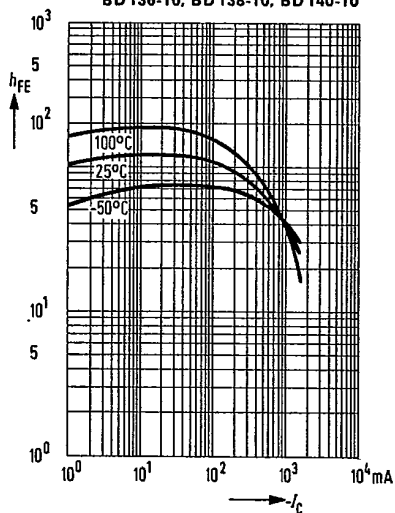
$V_{CE} = 2\text{ V}$; T_{amb} = parameter

(common emitter configuration)

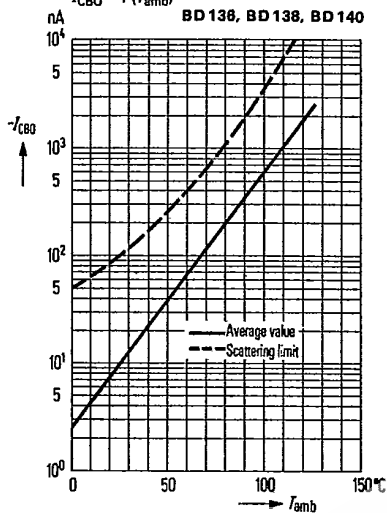
BD 136, BD 138, BD 140



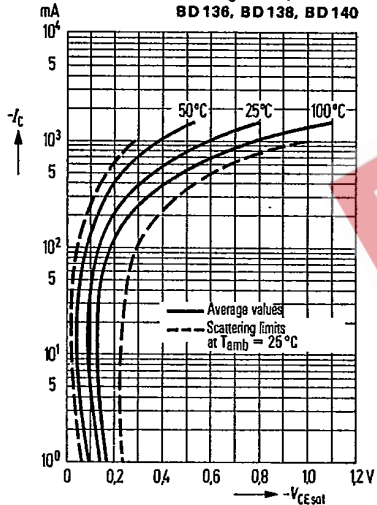
DC current gain $h_{FE} = f(I_C)$
 $V_{CE} = 2 \text{ V}$; $T_{amb} = \text{parameter}$
BD 136-10, BD 138-10, BD 140-10



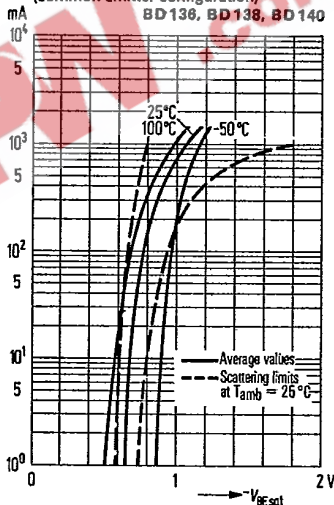
Collector cutoff current versus temperature
 $I_{CBO} = f(T_{amb})$
BD 136, BD 138, BD 140



Collector-emitter saturation voltage
 $V_{CEsat} = f(I_C)$
 $h_{FE} = 10$; $T_{amb} = \text{parameter}$
(common emitter configuration)
BD 136, BD 138, BD 140

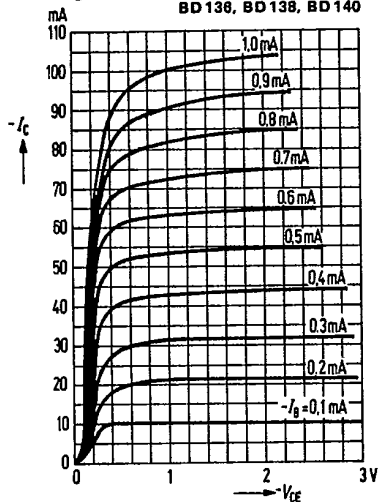


Base-emitter saturation voltage
 $V_{BEsat} = f(I_C)$
 $h_{FE} = 10$; $T_{amb} = \text{parameter}$
(common emitter configuration)
BD 136, BD 138, BD 140



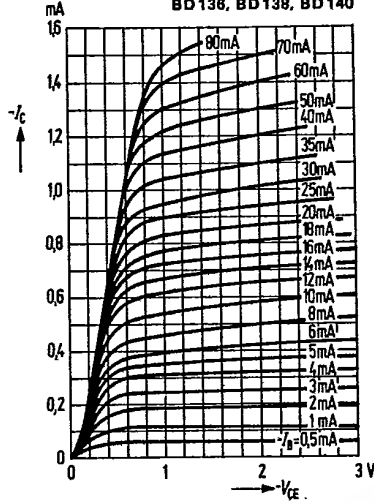
Output characteristics $I_C = f(V_{CE})$
 $I_B = \text{parameter}$

BD 136, BD 138, BD 140



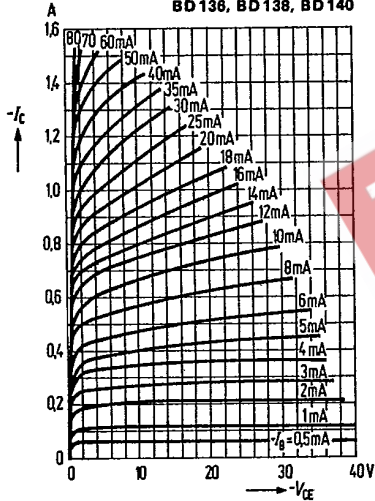
Output characteristics $I_C = f(V_{CE})$
 $I_B = \text{parameter}$

BD 136, BD 138, BD 140



Output characteristics $I_C = f(V_{CE})$
 $I_B = \text{parameter}$

BD 136, BD 138, BD 140



Transition frequency $f_T = f(I_C)$
 $-V_{CE} = 10 \text{ V}$

BD 136, BD 138, BD 140

